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RESPONSE UNDER 37 C.F.R. § 1.116
EXPEDITED PROCEDURE
GROUP 2881
PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Toshiro HAYAKAWA, et al.

Appln. No.: 09/315,068

Group Art Unit: 2881

Filed: May 20, 1999

Examiner: Jeffrey N. Zahn

For: SEMICONDUCTOR LASER AND METHOD OF MANUFACTURING THE SAME

RESPONSE UNDER 37 C.F.R. § 1.116

ATTN: BOX AF
Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action dated November 1, 2001, please consider the remarks as submitted herewith.

REMARKS

Claims 1-6 are all the claims pending in the application. Claims 3 and 4 were withdrawn from consideration pursuant to a restriction requirement.

Claims 1-2 and 5-6 are rejected under 35 U.S.C. § 103(a) as unpatentable over U.S. Patent 4,728,628 to Fiddymen *et al.* (herein "Fiddymen") in view of "High-Power High-Efficiency 0.98 μ m Wavelength InGaAs-(In)GaAs(P)-InGaP Broadened Waveguide Lasers Grown by Gas- Source Molecular Beam Epitaxy," IEEE Journal of Quantum Electronics, Vol. 33, No. 12, pages 2266-2276, by Gokhale *et al.* ("herein Gokhale") and "A study of structures

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